

Augustinas Galeckas

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

143
papers

2,273
citations

24
h-index

43
g-index

151
ext. papers

2,524
ext. citations

3
avg, IF

4.76
L-index

#	Paper	IF	Citations
143	Retinal injuries in seven teenage boys from the same handheld laser. <i>American Journal of Ophthalmology Case Reports</i> , 2022 , 27, 101596	1.3	0
142	ZnSnN ₂ in Real Space and k-Space: Lattice Constants, Dislocation Density, and Optical Band Gap. <i>Advanced Optical Materials</i> , 2021 , 9, 2100015	8.1	0
141	Visible Light Driven Photocatalytic Decolorization and Disinfection of Water Employing Reduced TiO ₂ Nanopowders. <i>Catalysts</i> , 2021 , 11, 228	4	6
140	Enhancing the UV Emission in ZnO-CNT Hybrid Nanostructures via the Surface Plasmon Resonance of Ag Nanoparticles. <i>Nanomaterials</i> , 2021 , 11,	5.4	2
139	Water Vapor Photoelectrolysis in a Solid-State Photoelectrochemical Cell with TiO Nanotubes Loaded with CdS and CdSe Nanoparticles. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 46875-46885	9.5	2
138	Conversion pathways of primary defects by annealing in proton-irradiated n-type 4H-SiC. <i>Physical Review B</i> , 2020 , 102,	3.3	20
137	Selective etching of nanostructured a-Si:Al and its effect on porosity, Al gradient and surface oxidation. <i>Thin Solid Films</i> , 2020 , 702, 137982	2.2	0
136	Influence of hydrogen implantation on emission from the silicon vacancy in 4H-SiC. <i>Journal of Applied Physics</i> , 2020 , 127, 085701	2.5	5
135	Effects of annealing on photoluminescence and defect interplay in ZnO bombarded by heavy ions: Crucial role of the ion dose. <i>Journal of Applied Physics</i> , 2020 , 127, 025701	2.5	1
134	Impact of post annealing and hydrogen implantation on functional properties of Cu ₂ O thin films for photovoltaic applications. <i>Journal of Alloys and Compounds</i> , 2020 , 825, 153982	5.7	5
133	Optical signatures of single ion tracks in ZnO. <i>Nanoscale Advances</i> , 2020 , 2, 724-733	5.1	4
132	Al incorporation during metal organic chemical vapour deposition of aluminium zinc oxide. <i>Thin Solid Films</i> , 2020 , 709, 138245	2.2	1
131	Strain Modulation of Si Vacancy Emission from SiC Micro- and Nanoparticles. <i>Nano Letters</i> , 2020 , 20, 8689-8695	11.5	4
130	Acceptor complex signatures in oxygen-rich ZnO thin films implanted with chlorine ions. <i>Journal of Applied Physics</i> , 2020 , 128, 125701	2.5	1
129	Muon Interaction with Negative-U and High-Spin-State Defects: Differentiating Between C and Si Vacancies in 4H-SiC. <i>Physical Review Applied</i> , 2020 , 14,	4.3	4
128	Evidence of defect band mechanism responsible for band gap evolution in (ZnO) _{1-x} (GaN) _x alloys. <i>Physical Review B</i> , 2019 , 100,	3.3	4
127	Surface Effects and Optical Properties of Self-Assembled Nanostructured a-Si:Al. <i>Nanomaterials</i> , 2019 , 9,	5.4	3

126	Selective photocurrent generation in HfO ₂ and carbon nanotube hybrid nanocomposites under Ultra-Violet and visible photoexcitations. <i>Materials Letters</i> , 2019 , 246, 45-48	3.3	5
125	Annealing Kinetics of the Interstitial CarbonDioxygen Complex in Silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800986	1.6	3
124	Role of intrinsic and extrinsic defects in H implanted hydrothermally grown ZnO. <i>Journal of Applied Physics</i> , 2019 , 126, 125707	2.5	7
123	Broad luminescence from donor-complexed LiZn and NaZn acceptors in ZnO. <i>Physical Review B</i> , 2019 , 100,	3.3	5
122	Time evolution of ZnO-CNT photoluminescence under variable ambient and temperature conditions. <i>IOP Conference Series: Materials Science and Engineering</i> , 2019 , 613, 012031	0.4	1
121	Electrical charge state identification and control for the silicon vacancy in 4H-SiC. <i>Npj Quantum Information</i> , 2019 , 5,	8.6	38
120	Monitoring selective etching of self-assembled nanostructured a-Si:Al films. <i>Nanotechnology</i> , 2019 , 30, 135601	3.4	2
119	The temperature-dependency of the optical band gap of ZnO measured by electron energy-loss spectroscopy in a scanning transmission electron microscope. <i>Journal of Applied Physics</i> , 2018 , 123, 145111	4.5	6
118	Improving carrier transport in CuO thin films by rapid thermal annealing. <i>Journal of Physics Condensed Matter</i> , 2018 , 30, 075702	1.8	17
117	Photoluminescence Properties of Photochromic Yttrium Hydride Films Containing Oxygen. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1800139	1.3	2
116	Boron-doping of cubic SiC for intermediate band solar cells: a scanning transmission electron microscopy study. <i>SciPost Physics</i> , 2018 , 5,	6.1	2
115	Optical and Microstructural Investigation of Heavy B-Doping Effects in Sublimation-Grown 3C-SiC. <i>Materials Science Forum</i> , 2018 , 924, 221-224	0.4	1
114	(Invited) Controlling the Carbon Vacancy in 4H-SiC by Thermal Processing. <i>ECS Transactions</i> , 2018 , 86, 91-97	1	2
113	Phase stability and strain accumulation in CdO as a function of Cd/O supply during MOVPE synthesis. <i>Superlattices and Microstructures</i> , 2018 , 120, 569-577	2.8	
112	Controllable template approach for ZnO nanowire growth. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600480	1.6	2
111	Depth-Resolved Carrier Lifetime Measurements in 4H-SiC Epilayers Monitoring Carbon Vacancy Elimination. <i>Materials Science Forum</i> , 2017 , 897, 258-261	0.4	2
110	Characterization of B-Implanted 3C-SiC for Intermediate Band Solar Cells. <i>Materials Science Forum</i> , 2017 , 897, 299-302	0.4	1
109	Normal and reverse defect annealing in ion implanted II-VI oxide semiconductors. <i>Journal of Applied Physics</i> , 2017 , 122, 115701	2.5	9

108	Influence of the Interface on the Photoluminescence Properties in ZnO Carbon-Based Nanohybrids. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 14879-14887	3.8	12
107	Investigations on new carbon-based nanohybrids combining carbon nanotubes, HfO ₂ and ZnO nanoparticles. <i>IOP Conference Series: Materials Science and Engineering</i> , 2017 , 175, 012064	0.4	
106	Self-diffusion measurements in isotopic heterostructures of undoped and in situ doped ZnO: Zinc vacancy energetics. <i>Physical Review B</i> , 2016 , 94,	3.3	14
105	Boron-Implanted 3C-SiC for Intermediate Band Solar Cells. <i>Materials Science Forum</i> , 2016 , 858, 291-294	0.4	5
104	Local homoepitaxy of zinc oxide thin films by magnetron sputtering. <i>Thin Solid Films</i> , 2016 , 601, 18-21	2.2	2
103	Cubic silicon carbide as a potential photovoltaic material. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 145, 104-108	6.4	32
102	Photocurrent generation in carbon nanotube/cubic-phase HfO ₂ nanoparticle hybrid nanocomposites. <i>Beilstein Journal of Nanotechnology</i> , 2016 , 7, 1075-85	3	10
101	A Review of the Synthesis and Photoluminescence Properties of Hybrid ZnO and Carbon Nanomaterials. <i>Journal of Nanomaterials</i> , 2016 , 2016, 1-12	3.2	41
100	The Band Gap of BaPrO ₃ Studied by Optical and Electrical Methods. <i>Journal of the American Ceramic Society</i> , 2016 , 99, 492-498	3.8	2
99	The influence of Fe impurities on the annealing of OH \square i complexes in ZnO. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 273-278	1.3	4
98	Improvements in Realizing 4H-SiC Thermal Neutron Detectors. <i>EPJ Web of Conferences</i> , 2016 , 106, 05004	4.3	7
97	Metal oxide nanoparticles embedded in rare-earth matrix for low temperature thermal imaging applications. <i>Materials Research Express</i> , 2016 , 3, 055010	1.7	4
96	One Step Synthesis of Pure Cubic and Monoclinic HfO ₂ Nanoparticles: Effects of Temperature and Ambient on the Photoluminescent Properties. <i>ECS Transactions</i> , 2015 , 64, 19-28	1	0
95	Optical activity and defect/dopant evolution in ZnO implanted with Er. <i>Journal of Applied Physics</i> , 2015 , 118, 125703	2.5	29
94	Study of Photoluminescence Properties of Cu _x O Thin Films Prepared by Reactive Radio Frequency Magnetron Sputtering. <i>Materials Research Society Symposia Proceedings</i> , 2015 , 1792, 1		1
93	A comparative study of 1.5 μ m photoluminescence from (Er, Si) and (Er, Ge) co-sputtered with Al ₂ O ₃ on Si. <i>Journal of Alloys and Compounds</i> , 2014 , 590, 5-8	5.7	
92	Tunneling in ZnO/ZnCdO quantum wells towards next generation photovoltaic cells. <i>Solar Energy</i> , 2014 , 106, 82-87	6.8	10
91	. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 2105-2111	1.7	17

90	Effects of temperature, triazole and hot-pressing on the performance of TiO ₂ photoanode in a solid-state photoelectrochemical cell. <i>Electrochimica Acta</i> , 2014 , 115, 66-74	6.7	8
89	Photoluminescent cubic and monoclinic HfO ₂ nanoparticles: effects of temperature and ambient. <i>Materials Research Express</i> , 2014 , 1, 015035	1.7	23
88	ALD Applied to Conformal Rare-Earth Coating of ZnO Nanoparticles for Low Temperature Thermal Imaging Applications. <i>ECS Transactions</i> , 2014 , 64, 23-31	1	2
87	Nuclear Radiation Detectors Based on 4H-SiC p+-n Junction. <i>Materials Science Forum</i> , 2014 , 778-780, 1046-1049	0.4	4
86	Influence of graphene synthesizing techniques on the photocatalytic performance of graphene-TiO ₂ nanocomposites. <i>Physical Chemistry Chemical Physics</i> , 2013 , 15, 15528-37	3.6	37
85	Basic optical and electronic properties of Ag ₂ Cu ₂ O ₃ crystalline films. <i>Thin Solid Films</i> , 2013 , 531, 185-188.	2	3
84	Selective nano-emitter fabricated by silver assisted chemical etch-back for multicrystalline solar cells. <i>RSC Advances</i> , 2013 , 3, 15483	3.7	15
83	PL and DLTS Analysis of Carbon-Related Centers in Irradiated P-Type Cz-Si. <i>Solid State Phenomena</i> , 2013 , 205-206, 224-227	0.4	4
82	Solid-state photoelectrochemical H ₂ generation with gaseous reactants. <i>Electrochimica Acta</i> , 2013 , 97, 320-325	6.7	23
81	Nano-structuring in SiGe by oxidation induced anisotropic Ge self-organization. <i>Journal of Applied Physics</i> , 2013 , 113, 104310	2.5	8
80	Photoluminescence of reactively sputtered Ag ₂ O films. <i>Thin Solid Films</i> , 2013 , 536, 156-159	2.2	11
79	Carrier dynamics in linearly and step graded bandgap Zn _{1-x} Cd _x O structures. <i>Applied Physics Letters</i> , 2013 , 102, 191916	3.4	2
78	Engineering of optically defect free Cu ₂ O enabling exciton luminescence at room temperature. <i>Optical Materials Express</i> , 2013 , 3, 2072	2.6	30
77	One-dimensional WO ₃ and its hydrate: One-step synthesis, structural and spectroscopic characterization. <i>Journal of Solid State Chemistry</i> , 2012 , 185, 245-252	3.3	17
76	Engineering of nearly strain-free ZnO films on Si(1 1 1) by tuning AlN buffer thickness. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1476-1480	2.8	3
75	ALD Applied to Conformal Coating of Nanoporous γ -Alumina: Spinel Formation and Luminescence Induced by Europium Doping. <i>Journal of the Electrochemical Society</i> , 2012 , 159, P45-P49	3.9	10
74	Zinc vacancy and oxygen interstitial in ZnO revealed by sequential annealing and electron irradiation. <i>Physical Review B</i> , 2012 , 86,	3.3	129
73	Testing ZnO based photoanodes for PEC applications. <i>Energy Procedia</i> , 2012 , 22, 101-107	2.3	9

72	A comparative analysis of oxidation rates for thin films of SiGe versus Si. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 1934-1939	1.6	6
71	One step synthesis of pure cubic and monoclinic HfO ₂ nanoparticles: Correlating the structure to the electronic properties of the two polymorphs. <i>Journal of Applied Physics</i> , 2012 , 112, 104107	2.5	35
70	Time-resolved spectroscopy of carrier dynamics in graded ZnCd _x O multilayer structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1805-1808		1
69	Optical and electrical properties of reactively sputtered Ag ₂ Cu ₂ O ₃ films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1590-1592		1
68	Unusual Photoluminescence of CaHfO ₃ and SrHfO ₃ Nanoparticles. <i>Advanced Functional Materials</i> , 2012 , 22, 1174-1179	15.6	42
67	Response to [Comment on Unusual Photoluminescence of CaHfO ₃ and SrHfO ₃ Nanoparticles]	15.6	2
66	Ge concentrations in pile-up layers of sub-100-nm SiGe films for nano-structuring by thermal oxidation. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 041212	1.3	11
65	Ge redistribution in SiO ₂ /SiGe structures under thermal oxidation: Dynamics and predictions. <i>Journal of Applied Physics</i> , 2012 , 111, 024308	2.5	15
64	Understanding phase separation in ZnCdO by a combination of structural and optical analysis. <i>Physical Review B</i> , 2011 , 83,	3.3	43
63	Precursor-Dependent Blue-Green Photoluminescence Emission of ZnO Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2011 , 115, 25227-25233	3.8	48
62	MgZnO synthesis employing weak oxidants for accurate Mg incorporation control. <i>Journal of Crystal Growth</i> , 2011 , 333, 66-69	1.6	1
61	Tuning light absorption by band gap engineering in ZnCdO as a function of MOVPE-synthesis conditions and annealing. <i>Journal of Crystal Growth</i> , 2011 , 315, 301-304	1.6	20
60	Structural, optical and electrical properties of reactively sputtered Ag ₂ Cu ₂ O ₃ films. <i>Thin Solid Films</i> , 2011 , 520, 230-234	2.2	4
59	On the mechanism of enhanced photocatalytic activity of composite TiO ₂ /carbon nanofilms. <i>Applied Catalysis B: Environmental</i> , 2011 , 106, 337-342	21.8	22
58	Optical absorption related to Fe impurities in TlGaSe ₂ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 2186-2192	1.6	6
57	ALD Applied to Conformal Coating of Nanoporous γ -Alumina: Spinel Formation and Luminescence Induced by Europium Doping. <i>ECS Transactions</i> , 2011 , 41, 123-130	1	6
56	(Invited) Degradation of SiC Bipolar Devices: A Review of Likely Causes and Recent Advances in its Understanding. <i>ECS Transactions</i> , 2011 , 41, 225-236	1	8
55	Deep level related photoluminescence in ZnMgO. <i>Applied Physics Letters</i> , 2010 , 97, 211901	3.4	58

54	An investigation of Fe-doped ZnO thin films grown by magnetron sputtering. <i>Physica Scripta</i> , 2010 , T141, 014004	2.6	6
53	Structural and optical properties of polar and non-polar ZnO films grown by MOVPE. <i>Journal of Crystal Growth</i> , 2008 , 310, 5020-5024	1.6	17
52	Fundamental band edge absorption in nominally undoped and doped 4H-SiC. <i>Journal of Applied Physics</i> , 2007 , 101, 123521	2.5	39
51	Investigation of Structural Stability in 4H-SiC Structures with Heavy Ion Implanted Interface. <i>Materials Science Forum</i> , 2006 , 527-529, 395-398	0.4	2
50	Combined photoluminescence-imaging and deep-level transient spectroscopy of recombination processes at stacking faults in 4H-SiC. <i>Physical Review B</i> , 2006 , 74,	3.3	40
49	Effect of substrate proximity on luminescence yield from Si nanocrystals. <i>Applied Physics Letters</i> , 2006 , 89, 111124	3.4	9
48	Recombination-induced stacking faults: evidence for a general mechanism in hexagonal SiC. <i>Physical Review Letters</i> , 2006 , 96, 025502	7.4	109
47	Size-reduced silicon nanowires: Fabrication and electrical characterization. <i>Materials Science and Engineering C</i> , 2005 , 25, 733-737	8.3	14
46	Single dot optical spectroscopy of silicon nanocrystals: low temperature measurements. <i>Optical Materials</i> , 2005 , 27, 973-976	3.3	16
45	Investigation of Stacking Fault Formation in Hydrogen Bombarded 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 327-330	0.4	5
44	Optical Investigation of the Built-In Strain in 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2004 , 457-460, 657-660	0.4	3
43	Two-Photon Spectroscopy of 4H-SiC by Using Laser Pulses at Below-Gap Frequencies. <i>Materials Science Forum</i> , 2004 , 457-460, 605-608	0.4	6
42	Microstructural Aspects and Mechanism of Degradation of 4H-SiC PIN Diodes under Forward Biasing. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 815, 223		6
41	Time-resolved analysis of the white photoluminescence from SiO ₂ films after Si and C coimplantation. <i>Applied Physics Letters</i> , 2004 , 84, 25-27	3.4	24
40	Characterization of carrier lifetime and diffusivity in 4H-SiC using time-resolved imaging spectroscopy of electroluminescence. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 102, 304-307	3.1	9
39	In Situ Studies of Structural Instability in Operating 4H-SiC PIN Diodes. <i>Materials Science Forum</i> , 2003 , 433-436, 933-936	0.4	6
38	SEM Visibility of Stacking Faults in 4H-Silicon Carbide Epitaxial and Implanted Layers. <i>Materials Science Forum</i> , 2003 , 433-436, 937-940	0.4	1
37	Temperature Dependence of the Absorption Coefficient in 4H- and 6H-Silicon Carbide at 355 nm Laser Pumping Wavelength. <i>Physica Status Solidi A</i> , 2002 , 191, 613-620		26

36	Improvement of an X-ray imaging detector based on a scintillating guides screen. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2002 , 487, 129-135	1.2	31
35	Recombination-enhanced extension of stacking faults in 4H-SiC p-i-n diodes under forward bias. <i>Applied Physics Letters</i> , 2002 , 81, 883-885	3.4	154
34	Characterization of 4H-SiC Band-Edge Absorption Properties by Free-Carrier Absorption Technique with a Variable Excitation Spectrum. <i>Materials Science Forum</i> , 2002 , 389-393, 617-620	0.4	4
33	Optical Emission Microscopy of Structural Defects in 4H-SiC PiN Diodes. <i>Materials Science Forum</i> , 2002 , 389-393, 431-434	0.4	3
32	Characterization of Al-implanted 4H SiC High Voltage Diodes. <i>Physica Scripta</i> , 2002 , T101, 207	2.6	2
31	Temperature Dependence of the Absorption Coefficient in 4H- and 6H-Silicon Carbide at 355 nm Laser Pumping Wavelength 2002 , 191, 613		1
30	Carrier lifetime investigation in 4H-SiC grown by CVD and sublimation epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 191-194	4.3	14
29	Investigation of Electroluminescence across 4H-SiC p+/n-/n+ Structures Using Optical Emission Microscopy. <i>Materials Science Forum</i> , 2001 , 353-356, 389-392	0.4	10
28	Optical characterization of excess carrier lifetime and surface recombination in 4H/6H-SiC. <i>Applied Physics Letters</i> , 2001 , 79, 365-367	3.4	52
27	Application of optical emission microscopy for reliability studies in 4H-SiC p+/n/n+ diodes. <i>Journal of Applied Physics</i> , 2001 , 90, 980-984	2.5	38
26	Spatially and time-resolved infrared absorption for optical and electrical characterization of indirect band gap semiconductors. <i>Thin Solid Films</i> , 2000 , 364, 181-185	2.2	5
25	Optical Characterization of 4H-SiC p+n-n+ Structures Applying Time- and Spectrally Resolved Emission Microscopy. <i>Materials Science Forum</i> , 2000 , 338-342, 683-686	0.4	3
24	Determination of the Polarization Dependence of the Free-Carrier-Absorption in 4H-SiC at High-Level Photoinjection. <i>Materials Science Forum</i> , 2000 , 338-342, 555-558	0.4	9
23	Electron Beam Induced Current Investigation of High-Voltage 4H Silicon Carbide Diodes. <i>Materials Science Forum</i> , 2000 , 338-342, 777-780	0.4	3
22	Time-resolved imaging of radiative recombination in 4H-SiC p-i-n diode. <i>Applied Physics Letters</i> , 1999 , 74, 3398-3400	3.4	19
21	Direct observation of excess carrier distribution in 4H-SiC power diodes. <i>IEEE Electron Device Letters</i> , 1999 , 20, 295-297	4.4	2
20	Band edge absorption, carrier recombination and transport measurements in 4H-SiC epilayers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 197-201	3.1	8
19	Investigation of surface recombination and carrier lifetime in 4H/6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 239-243	3.1	19

18	Analysis of the stretched exponential photoluminescence decay from nanometer-sized silicon crystals in SiO ₂ . <i>Journal of Applied Physics</i> , 1999 , 86, 6128-6134	2.5	295
17	Depth- and Time-Resolved Free Carrier Absorption in 4H SiC Epilayers: A Study of Carrier Recombination and Transport Parameters. <i>Materials Science Forum</i> , 1998 , 264-268, 529-532	0.4	6
16	Investigation of Excess Carrier Distributions in 4H-SiC Power Diodes under Static Conditions and Turn-On. <i>Materials Science Forum</i> , 1998 , 264-268, 1053-1056	0.4	1
15	Lateral and cross-well transport of highly and moderately excited carriers in Si _{1-x} Gex/Si superlattices. <i>Journal of Applied Physics</i> , 1998 , 83, 4756-4759	2.5	1
14	Observation of near-surface electrically active defects in n-type 6H-SiC. <i>Journal of Applied Physics</i> , 1998 , 83, 3649-3651	2.5	1
13	Evaluation of Auger Recombination Rate in 4H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 533-536	0.4	24
12	Auger recombination in 4H-SiC: Unusual temperature behavior. <i>Applied Physics Letters</i> , 1997 , 71, 3269-3271	2.5	97
11	Free carrier absorption and lifetime mapping in 4H SiC epilayers. <i>Journal of Applied Physics</i> , 1997 , 81, 3522-3525	2.5	23
10	Time-Resolved Photoluminescence from nm-Sized Silicon Crystallites In SiO ₂ . <i>Materials Research Society Symposia Proceedings</i> , 1997 , 486, 249		5
9	Time-resolved photoluminescence characterization of nm-sized silicon crystallites in SiO ₂ . <i>Thin Solid Films</i> , 1997 , 297, 167-170	2.2	36
8	Temporal and spatial investigation of 6 H-SiC by picosecond pulse excitation. <i>Physica Status Solidi A</i> , 1995 , 151, 219-229		3
7	Carrier Relaxation in a-Si:H/a-SiC:H Multilayers Studied by Picosecond Transient Reflectometry. <i>Physica Status Solidi (B): Basic Research</i> , 1995 , 190, 587-593	1.3	4
6	Ambipolar Diffusion Coefficients in a-SiC:H Alloys in Steady-State and Transient Grating Measurements. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 297, 497		3
5	Non-Equilibrium Carrier Dynamics in a-Si:H/a-SiC:H Multilayers. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 258, 553		7
4	Optical second harmonic generation in reflection from silicon carbide films. <i>Surface and Interface Analysis</i> , 1992 , 18, 71-72	1.5	3
3	Nonlinear optical investigation of silicon carbide surface properties. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1992 , 65, 357-360	1.2	6
2	Effective lifetime measurements in silicon-on-sapphire material by time-resolved reflectometry. <i>Thin Solid Films</i> , 1990 , 191, 37-45	2.2	2
1	Reflectivity and Dynamic Gratings in Implanted Si Induced by Picosecond Laser Pulses. <i>Physica Status Solidi (B): Basic Research</i> , 1988 , 150, 743-748	1.3	1

